

In the Claims:

~~11~~ Claim 2 (amended). The semiconductor configuration according to claim 1, wherein:

said first connection zone and said second connection zone define the lateral direction as extending from said first connection zone to said second connection zone;

at least one of said first and second connection zones has a first dimension in the vertical direction and a second dimension in the lateral direction; and

said second dimension is smaller than said first dimension.

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~~12~~ Claim 15 (amended). The semiconductor configuration according to claim 4, wherein said first dopant concentration is higher than  $10^{18} \text{ cm}^{-3}$ .

~~14~~  
~~2~~ Claim 16 (amended). The semiconductor configuration according to claim 4, wherein said second dopant concentration is substantially  $5 \times 10^{15} \text{ cm}^{-3}$ .